

211836US-2SRD RE



#9/A NE
7/10/02
Hayes

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
YASUO OHBA ET AL. : EXAMINER: JACKSON, J.
SERIAL NO: 09/915,710 :
FILED: JULY 27, 2001 : GROUP ART UNIT: 2815
FOR: SEMICONDUCTOR DEVICE AND:
METHOD OF FABRICATING THE
SAME

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

RECEIVED
JUN 25 2002
TECHNOLOGY CENTER 2800

SIR:

Responsive to the Office dated March 18, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claims 18-20 and 22 without prejudice.

Please amend the claims as indicated in the marked-up copy to read as follows:

17. (Amended) A semiconductor device comprising:

a substrate;

crystals formed on said substrate and containing at least Al and N, said crystals being disposed so as to expose portions of said substrate;

a thermal distortion reducing layer made of $Al_{1-u-v}Ga_uIn_vN$ ($0 \leq u \leq 1$, $0 \leq v \leq 1$, $u+v \leq 1$) formed on said crystals and having a different chemical formula from that of said crystals;

a first cladding layer formed over said thermal distortion reducing layer;